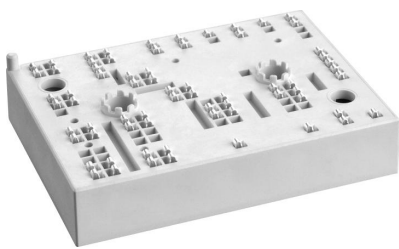


SKiiP 38NAB12T4V1



MiniSKiiP® 3

3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 38NAB12T4V1

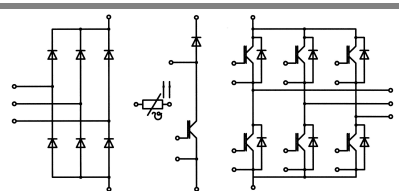
Target Data

Features

- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

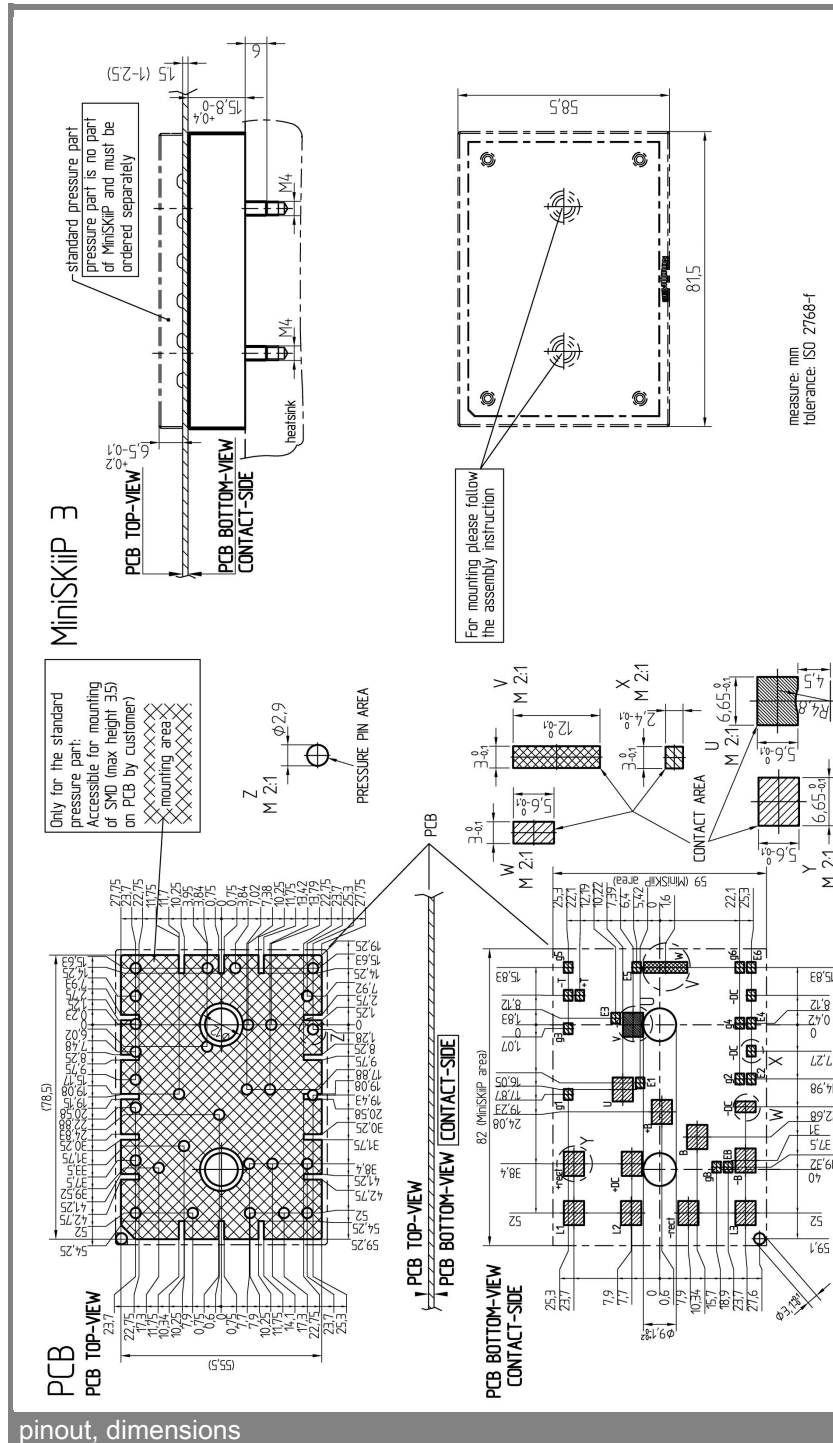
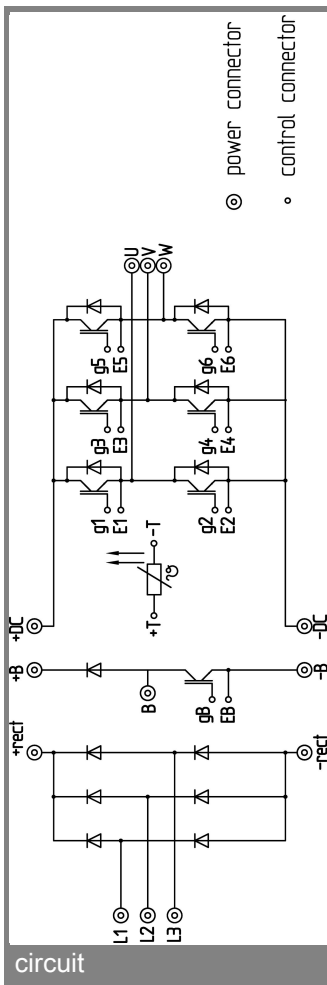
- V_{CEsat} , V_F = chip level value



NAB

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V _{CES}	T _s = 25 (70) °C t _p ≤ 1 ms	1200	V
I _C		115 (102)	A
I _{CRM}		300	A
V _{GES}		± 20	V
T _j		- 40 ... + 175	°C
Diode - Inverter, Chopper			
I _F	T _s = 25 (70) °C t _p ≤ 1 ms	103 (82)	A
I _{FRM}		300	A
T _j		- 40 ... + 175	°C
Diode - Rectifier			
V _{RRM}	T _s = 70 °C t _p = 10 ms, sin 180 °, T _j = 25 °C t _p = 10 ms, sin 180 °, T _j = 25 °C	1600	V
I _F		83	A
I _{FSM}		1000	A
i ² t		6600	A ² s
T _j		- 40 ... + 150	°C
I _{tRMS}		per power terminal (20 A / spring)	80
T _{stg}	T _{op} ≤ T _{stg}	- 40 ... + 125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V_{CEsat}	$I_{Cnom} = 100\text{ A, } T_j = 25\text{ (150) °C}$		1,8 (2,2)	2 (2,4)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5	5,8	6,5	V
$V_{CE(TO)}$	$T_j = 25\text{ (150) °C}$		1,1 (1)	1,3 (1,2)	V
r_T	$T_j = 25\text{ (150) °C}$		7 (12)	7 (12)	mΩ
C_{ies}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		-	-	nF
C_{oes}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		-	-	nF
C_{res}	$V_{CE} = 25\text{ V, } V_{GE} = 0\text{ V, } f = 1\text{ MHz}$		-	-	nF
$R_{th(j-s)}$	per IGBT		0,41		K/W
$t_{d(on)}$	under following conditions		-	-	ns
t_r	$V_{CC} = 600\text{ V, } V_{GE} = \pm 15\text{ V}$		-	-	ns
$t_{d(off)}$	$I_{Cnom} = 70\text{ A, } T_j = 150\text{ °C}$		-	-	ns
t_f	$R_{Gon} = R_{Goff} = -\Omega$		-	-	ns
E_{on}	inductive load		13,1		mJ
E_{off}			7,9		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_{Fnom} = 100\text{ A, } T_j = 25\text{ (150) °C}$		2,2 (2,1)	2,5 (2,45)	V
$V_{(TO)}$	$T_j = 25\text{ (150) °C}$		1,3 (0,9)	1,5 (1,1)	V
r_T	$T_j = 25\text{ (150) °C}$		9 (12)	10 (14)	mΩ
$R_{th(j-s)}$	per diode		0,62		K/W
I_{RRM}	under following conditions		-	-	A
Q_{rr}	$I_{Fnom} = 100\text{ A, } V_R = 300\text{ V}$		-	-	μC
E_{rr}	$V_{GE} = 0\text{ V, } T_j = 150\text{ °C}$ $di_F/dt = -\text{ A}/\mu\text{s}$		7,5		mJ
Diode - Rectifier					
V_F	$I_{Fnom} = 75\text{ A, } T_j = 25\text{ °C}$		1,2		V
$V_{(TO)}$	$T_j = 150\text{ °C}$		0,8		V
r_T	$T_j = 150\text{ °C}$		7		mΩ
$R_{th(j-s)}$	per diode		0,7		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
Mechanical Data					
w			95		g
M_s	Mounting torque	2		2,5	Nm



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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